

Notice of References Cited	Application/Control No. 10/660,561	Applicant(s)/Patent Under Reexamination LEE ET AL.	
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-2004/0077156	04-2004	Tsakalakos et al.	438/479
	C	US-6,596,377	07-2003	Hersee et al.	428/312.2
	D	US-5,948,470	09-1999	Harrison et al.	427/198
	E	US-5,705,321	01-1998	Brueck et al.	430/316
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	M	US-			

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.